

PHD**T2500A 3KV...SERIES****DISC TYPE THYRISTOR****Features**

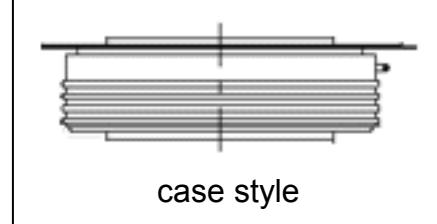
- Center amplifying gate
- Metal case with ceramic insulator
- tested according to IEC standards

2500A**Typical Applications**

- DC motor controls
- Controlled DC power supplies
- AC controllers

Major Ratings and Characteristics

Parameters	T2500A	Units
$I_{T(AV)}$	2500	A
	@ T_{hs}	°C
$I_{T(RMS)}$	4500	A
I_{TSM}	@ 50Hz	A
	@ 60Hz	A
I^2t	@ 50Hz	KA ² s
	@ 60Hz	KA ² s
$V_{DRM} \setminus V_{RRM}$	3000	V
T_q typical	200	μs
T_J range	- 40 to 125	°C



ELECTRICAL SPECIFICATIONS**Voltage Ratings**

Type number	Voltage Code	V_{RRM}/V_{DRM} , maximum repetitive peak reverse voltage V	V_{RSM} , maximum non- repetitive peak rev. voltage V	I_{RRM}/I_{DRM} max. @ $T_J = T_{J\max}$. mA
T2500A	24	2400	2500	250
	26	2600	2700	
	28	2800	2900	
	30	3000	3100	
	32	3200	3300	
	35	3500	3600	

On-state Conduction

Parameter	T2500A	Units	Conditions			
$I_{T(AV)}$	2500	A	180° conduction, half sine wave double side (single side) cooled			
	55	°C				
$I_{(RMS)}$	4600	A	DC @25 ° heatsink temperature double side cooled			
I_{TSM}	4600	A	$t = 10ms$	No voltage	Sinusoidal half wave, Initial $T_c = 125^\circ$	
	48200		$t = 8.3ms$	reapplied		
	36800		$t = 10ms$	50% V_{RRM}		
	38500		$t = 8.3ms$	reapplied		
$I^2 t$	10580	KA ² s	$t = 10ms$	No voltage		
	9640		$t = 8.3ms$	reapplied		
	6770		$t = 10ms$	50% V_{RRM}		
	6150		$t = 8.3ms$	reapplied		
V_{TM}	1.50	V	$I_{pk} = 2900A, T_c = 25^\circ$			
I_L	300	mA	$T_J = 25^\circ C, V_D = 5V$			

Switching

Parameter	T2500A	Units	Conditions
di/dt	Max. repetitive 50Hz (no repetitive) rate of rise of turned-on current	300 A/ μ s	From 67% V_{DRM} gate drive 20V, 20Ω , $t_r = 1\mu s$ $T_J = T_{J\max}$.
t_d	Maximum delay time	μ s	Gate drive 30V, 15Ω , $V_d = 67\% V_{DRM}$ $T_J = 25^\circ C$ Rise time $0.5 \mu s$
T_q	Typical turn-off time	μ s	$I_T = 800A$, $t_p = 1ms$, $T_J = T_{J\max}$, $di/dt = 20A/\mu s$, $V_R = 50V$ $dv/dt = 20V/\mu s$, $V_{DR} = 67\% V_{DRM}$

Blocking

Parameter	T2500A	Unit s	Conditions
dv/dt Maximum critical rate of rise of off-state voltage	500	V/μs	$T_J = T_{J\max}$ linear to 67% rated V_{DRM}
I_{DRM} Max. peak reverse and off-state leakage current	250	mA	$T_c = 25^\circ C$, rated V_{DRM}/V_{RRM} applied

Triggering

Parameter	T2500A	Units	Conditions
P_{GM} Maximum peak gate power	150	W	$t_p = 100 \mu s$
$P_{G(AV)}$ Maximum average gate power	10		
I_{GM} Max. peak positive gate current	30	A	Anode positive with respect to cathode
$+V_{GM}$ Maximum peak positive gate voltage	30	V	Anode positive with respect to cathode
$-V_{GM}$ Maximum peak negative gate voltage	0.25		Anode positive with respect to cathode
I_{GT} Maximum DC gate current required to trigger	400	mA	$T_c = 25^\circ C$, $V_{DRM}=5V$
V_{GT} Maximum gate voltage required to trigger	4	V	$T_c = 25^\circ C$, $V_{DRM}=5V$
V_{GD} DC gate voltage not to trigger	0.25	V	$T_c = 25^\circ C$ Max. gate current/ voltage not to trigger is the max. value which will not trigger any unit with rated V anode-to-cathode applied

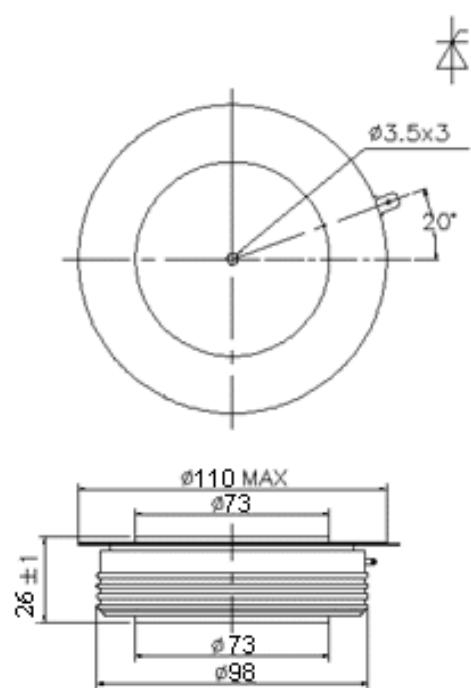
Thermal and Mechanical Specification

Parameter	T2500A	Units	Conditions
T_J Max. operating temperature	125	°C	
T_{Stg} Max. storage temperature range	-40 to 150		
$R_{th(J-C)}$ Thermal resistance, junction to case	0.019 0.0095	K/W	DC operation single side cooled DC operation double side cooled
$R_{th(C-h)}$ Thermal resistance, case to heatsink	0.004 0.002		Single side cooled Double side cooled
F Mounting torque, ± 10%	43000	Nm	Clamping force 43KN with Mounting compound
wt Approximate weight	1250	g	

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Outline Table



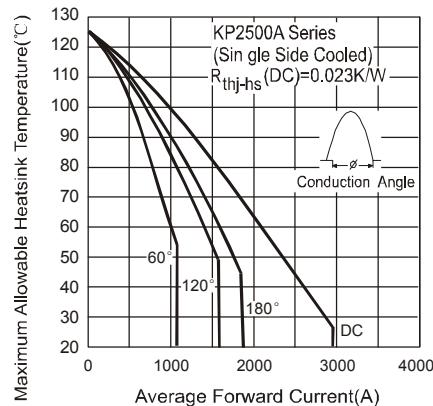


Fig.1-Current Ratings Characteristics

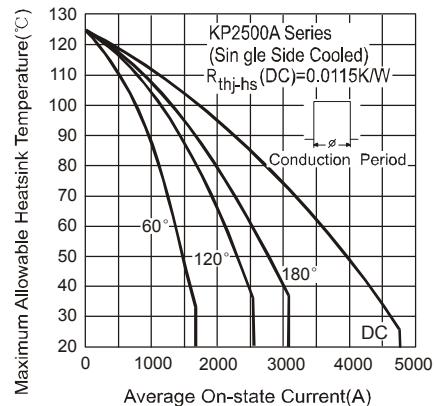


Fig.2-Current Ratings Characteristics

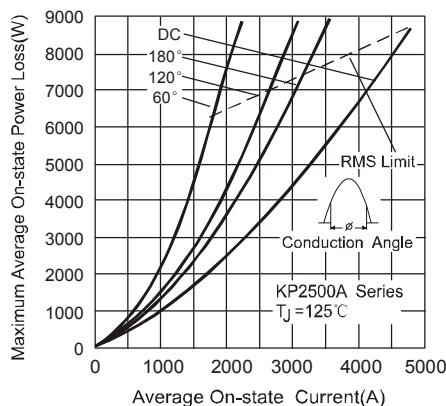


Fig.3-On-state Power Loss Characteristics

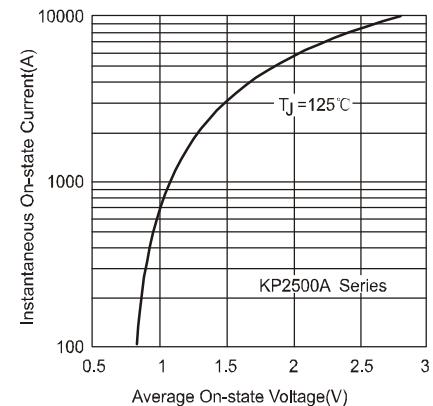
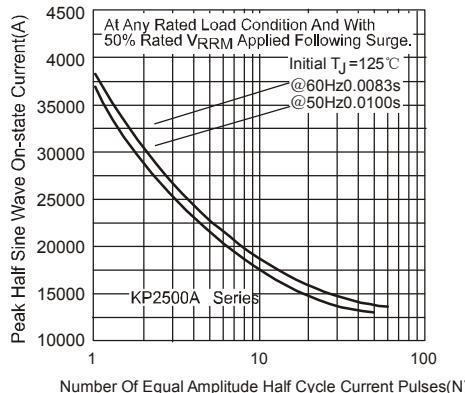
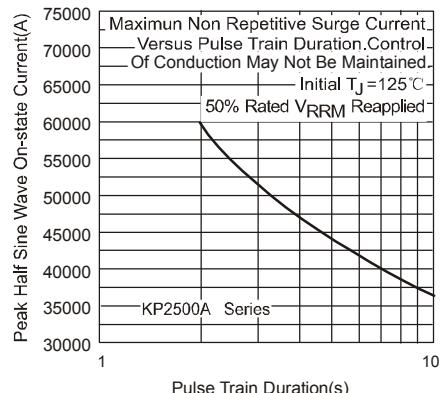
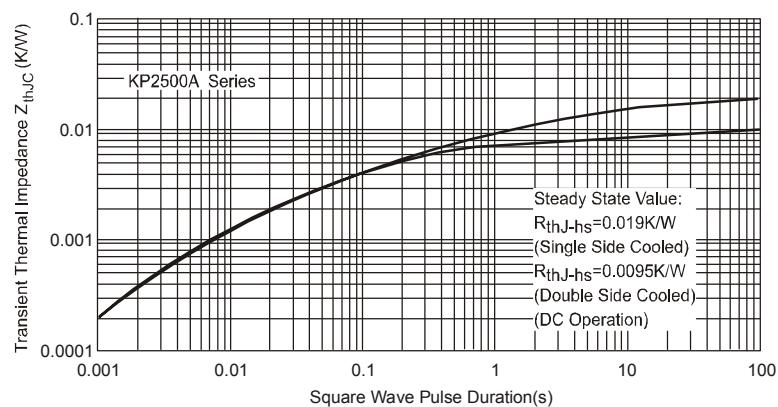


Fig.4-On-state Voltage Drop Characteristics

Fig.5-Maximum Non-Repetitive Surge Current
Single and Double Side CooledFig.6-Maximum Non-Repetitive Surge Current
Single and Double Side Cooled

Fig.7-Thermal Impedance Z_{thJC} Characteristics